

Molecular Conductivity Dopants and Charge Transfer Materials for High Efficiency OLEDs

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Pacific Northwest National Laboratory

OLED Materials for Lighting and Displays

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Outline

- ▶ **Conductivity doping**
- ▶ New charge transport layers
- ▶ Summary

The role of charge transport in producing efficient charge transport

► Efficiency

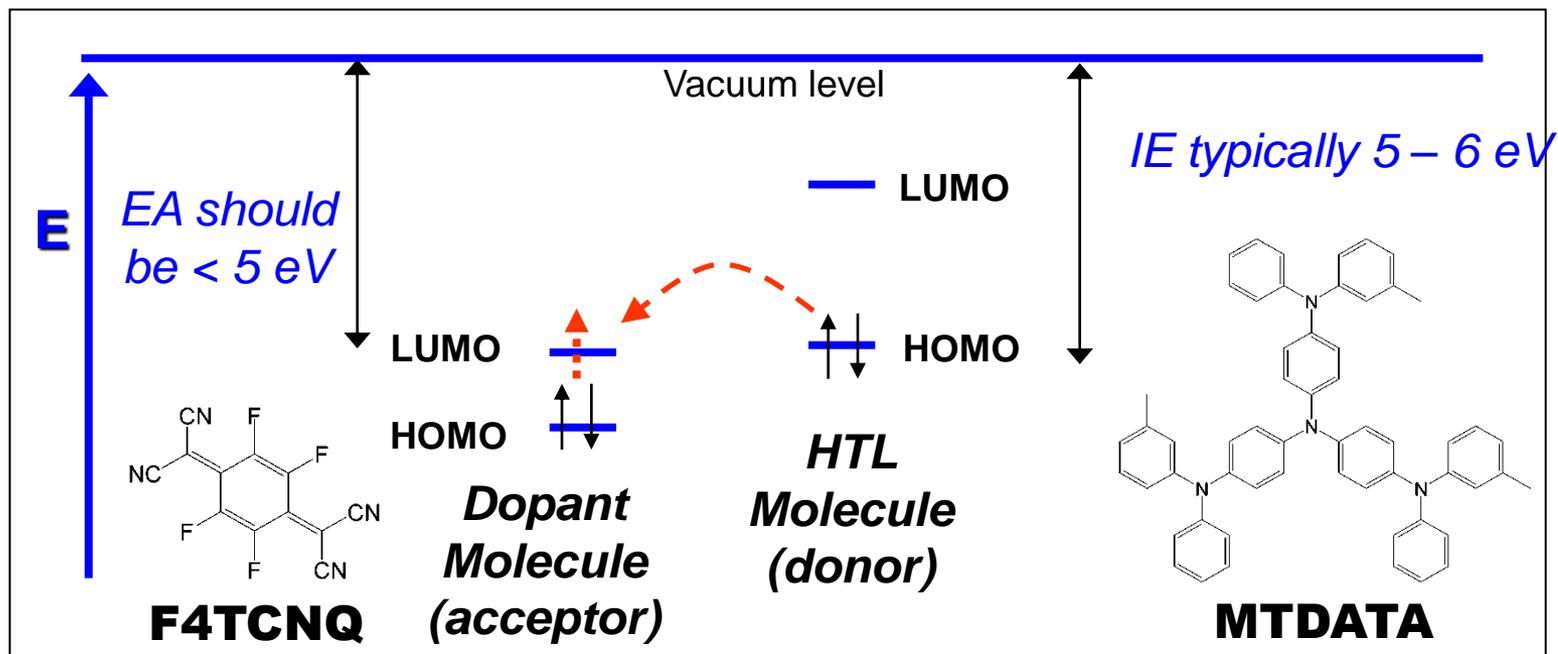
- Reduced injection barriers at interfaces
- Good charge transport
- Potential to reduce surface plasmon polariton coupling

► Cost

- Wider process window
- Potential for both solution and vacuum thermal processing



How do conductivity dopants work?

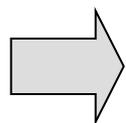


- ▶ Donate/accept electron to/from HTL/ETL to increase carrier density
- ▶ Mobility still governed by HTL (or ETL)
- ▶ Can be ionic (i.e., CsCO_3) or molecular (i.e., F4TCNQ)

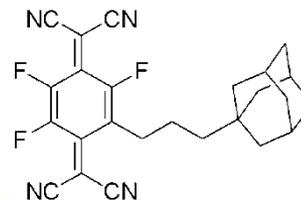
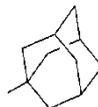
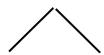
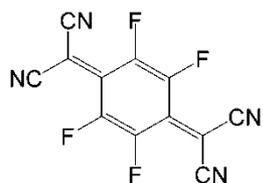
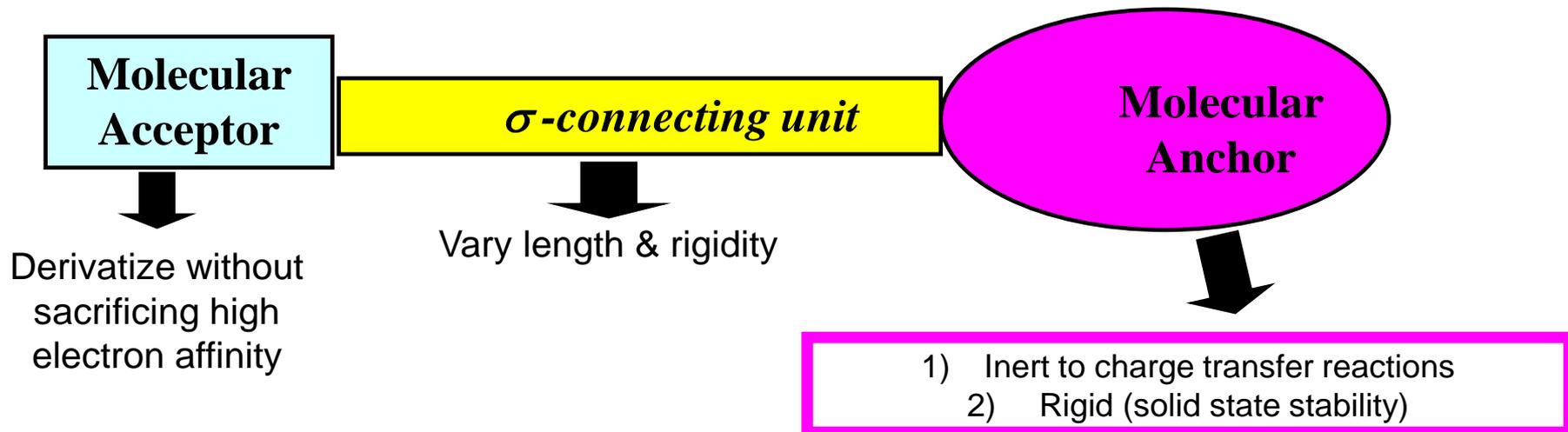
Challenges associated with some conductivity dopants

- ▶ Very reactive by nature
- ▶ Volatility and stability before, during and after deposition
- ▶ Must match energies appropriately
 - $\text{HOMO}_{\text{dopant}}$ to LUMO_{HTL}
 - $\text{LUMO}_{\text{dopant}}$ to HOMO_{ETL}
- ▶ Device stability – reduce dopant mobility in device (i.e., diffusion)
- ▶ One approach – add ‘anchor’ to improve stability

Initial project concept



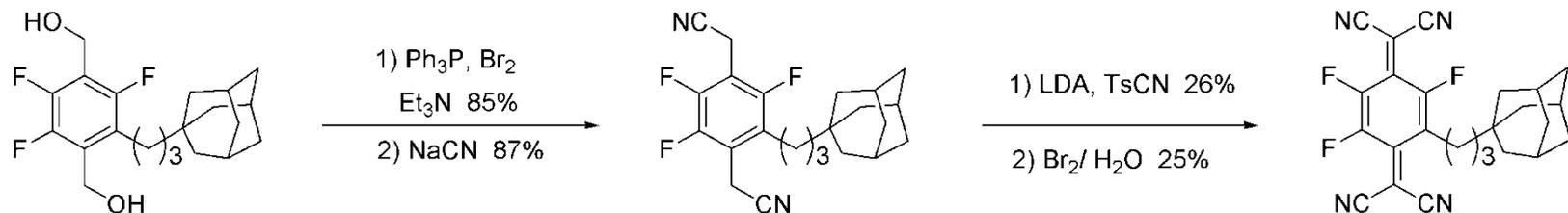
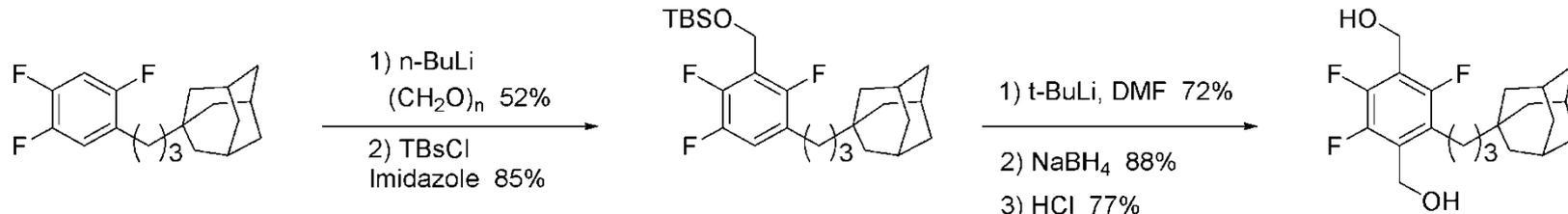
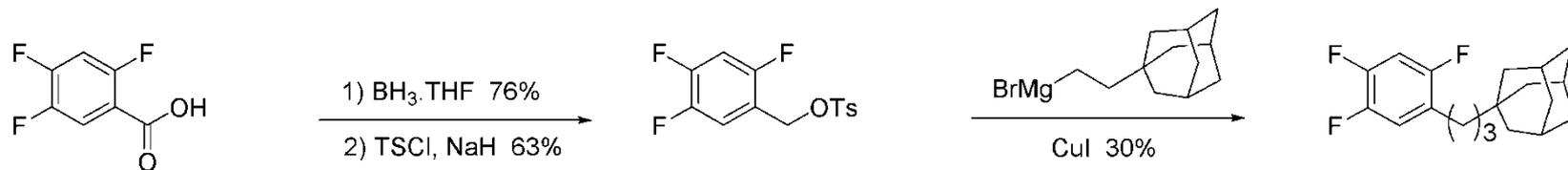
ANCHORED MOLECULAR DOPANT



F3TCNQ-Ad1

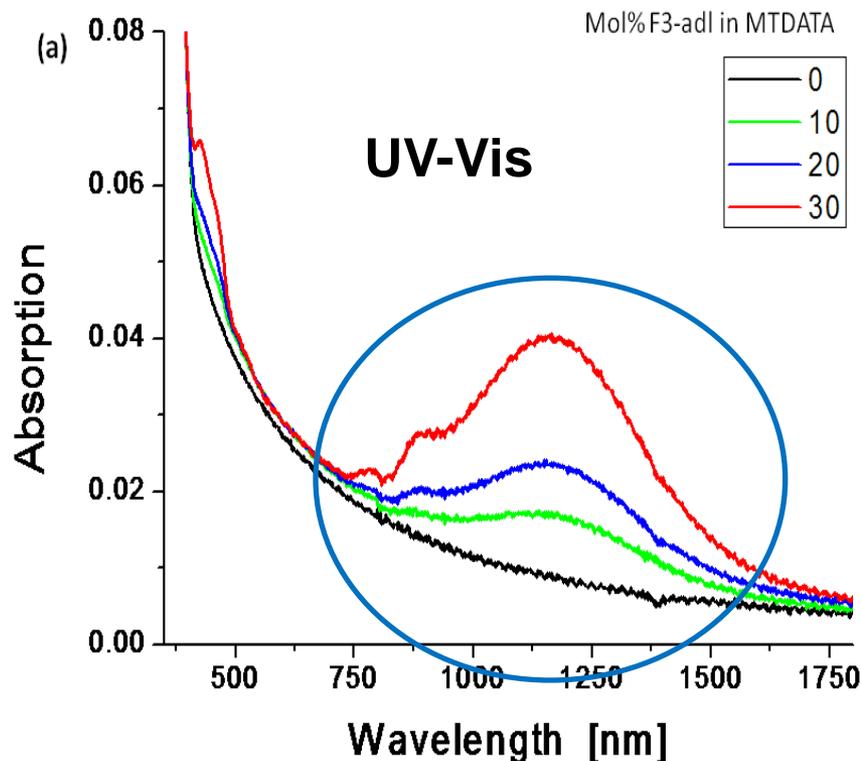
12 steps!

Synthesis and scale up of F3-TCNQ-Ad1

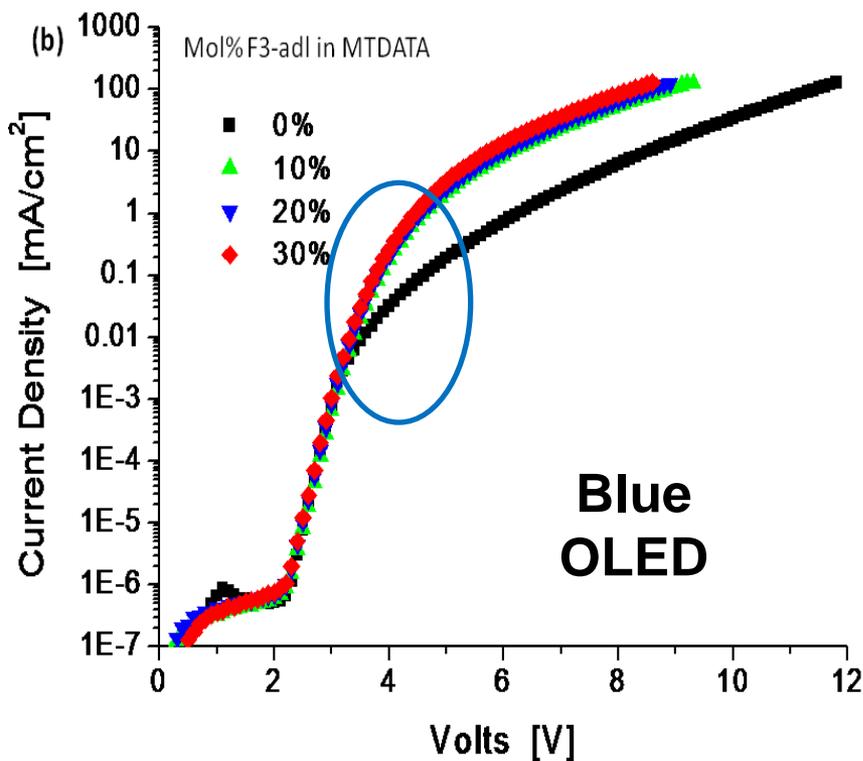


F3-TCNQ-Ad1

Anchored p-dopant generates charge complex and increases transport rate

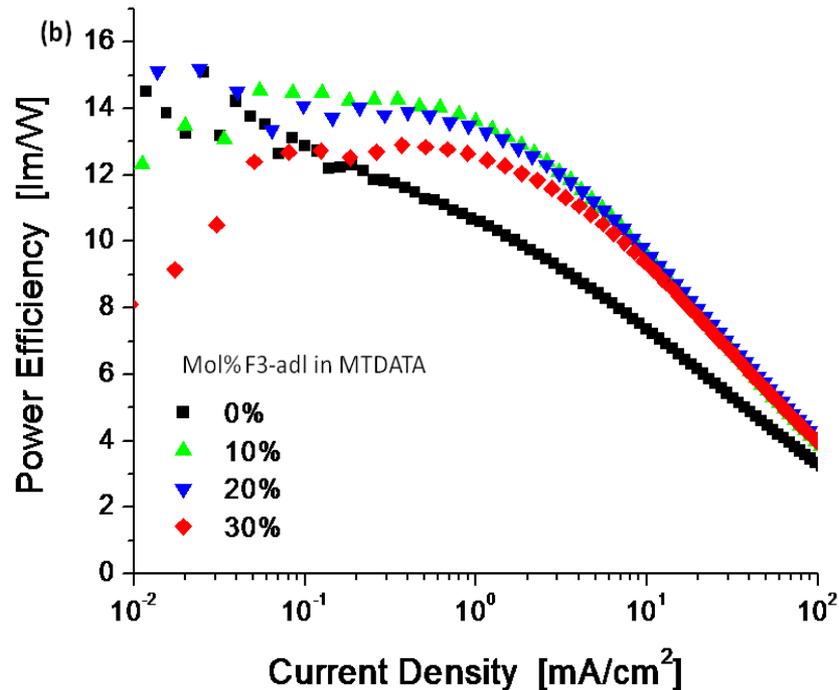
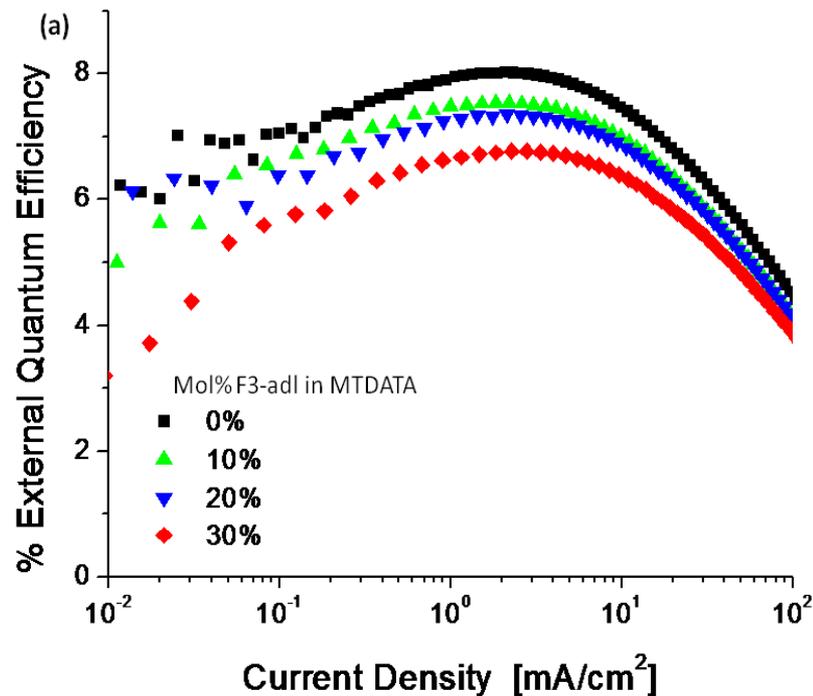


UV-Vis absorption spectra for solution-processed HTL (MTDATA:F3TCNQ-adl)



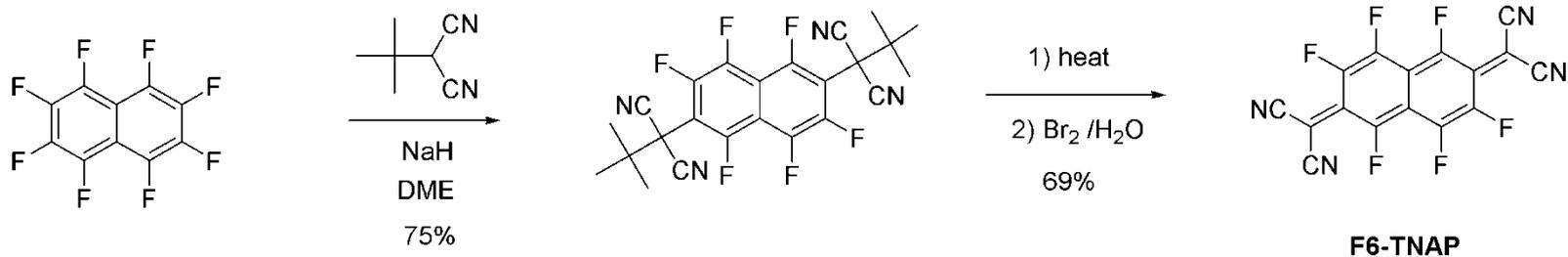
ITO/60 nm HTL:x mol% F3TCNQ-adl/5 nm TCTA/15 nm HM-A1:5 wt% Flrpic/50 nm PO15/1 nm LiF/100 nm Al

EQE and power efficiency blue OLED using anchored dopant F3TCNQ-adl



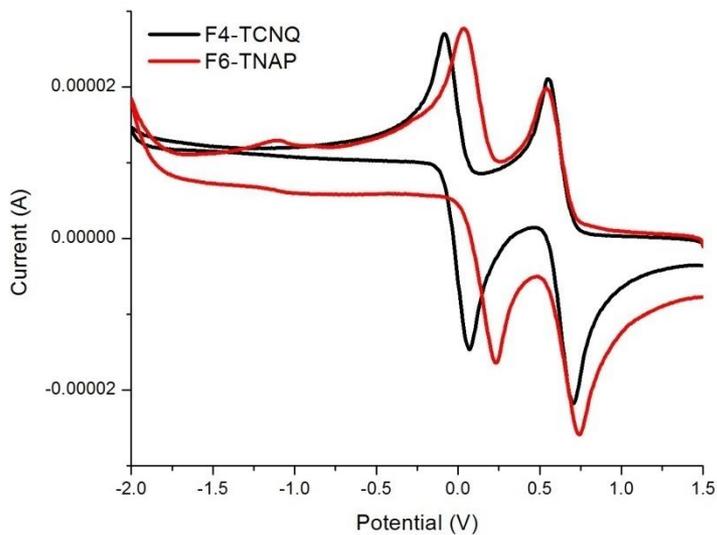
Or, increase MW...

- ▶ Structural analog to F4TCNQ
- ▶ F6-TNAP is obtained in 3 steps in good yield – amenable to scaleup
 - Sublimes well
 - Less volatile than F4TCNQ



P.K. Koech, A.B. Padmaperuma, et al., *Chem. Mater.*, **2010**, 22 (13), 3926–3932

Solution electrochemistry is similar to F4TCNQ

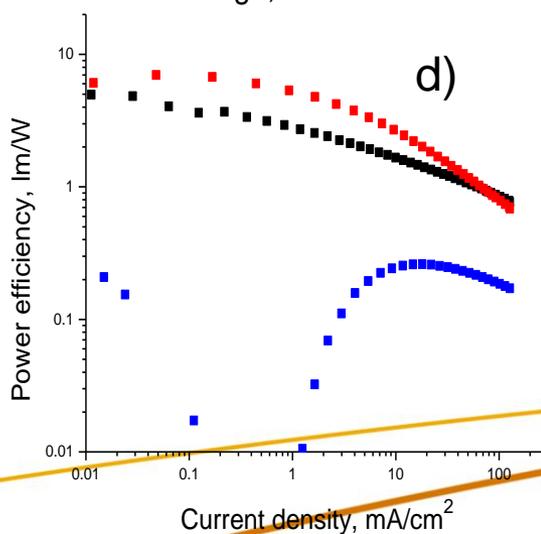
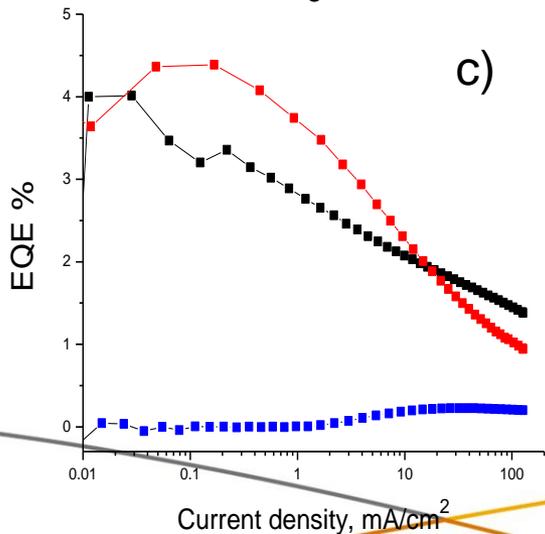
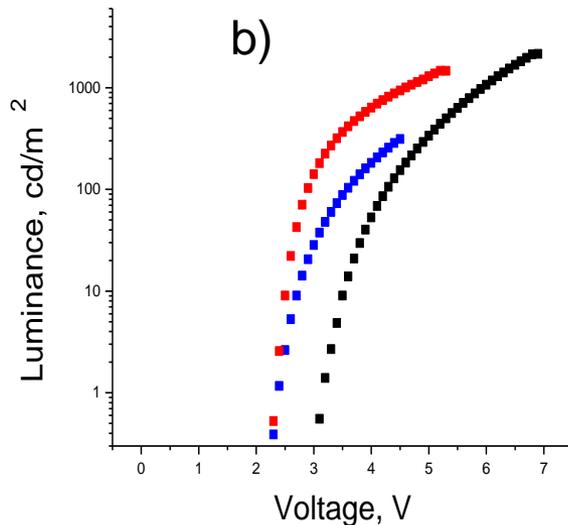
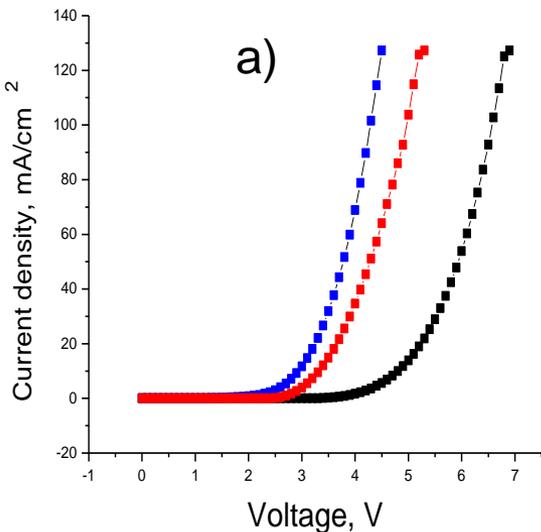


	From Experiment				Theory	
	E_{red} (V)	E_g (eV)	E_{LUMO} (eV)	E_{HOMO} (eV)	E_{LUMO} (eV)	E_{HOMO} (eV)
F4-TCNQ	0.63	2.98	- 5.35	- 8.33	- 5.51	- 7.96
F3-TCNQ-Ad1	0.50	2.86	- 5.22	- 8.08	- 4.95	- 7.36
F6-TNAP	0.65	2.10	- 5.37	- 7.47	- 5.57	- 7.48

$$E_{LUMO} = - 4.72 - E_{red}; E_{HOMO} = E_{LUMO} - E_g$$

- E_{LUMO} is similar to F4TCNQ – should dope, e.g., MTDATA

Red p-i-n OLEDs using F6-TNAP have better EQE, efficiency



Device structures:
HTL 30 nm*/EML 15 nm/ETL 50 nm*/
cathode 100nm
**excluding 5 nm buffers when applicable*

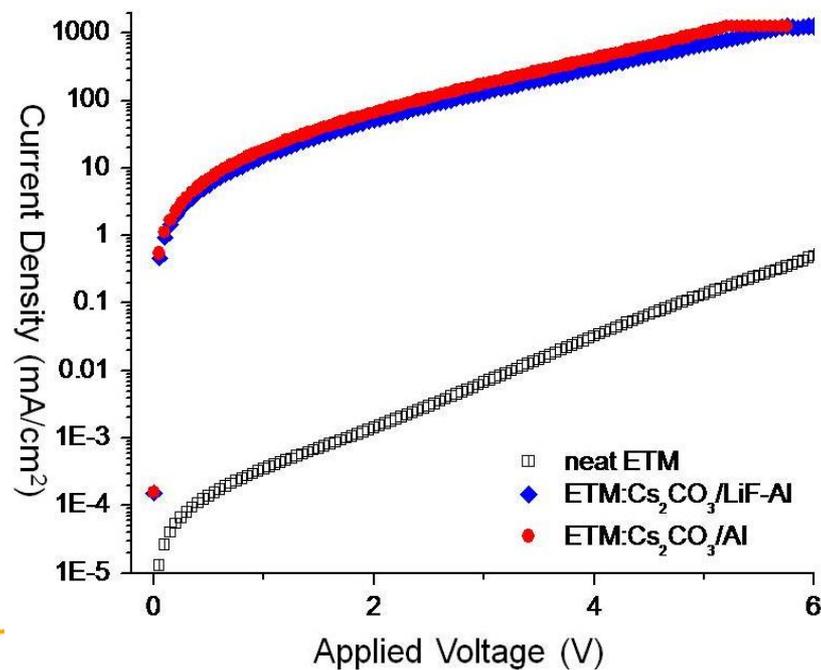
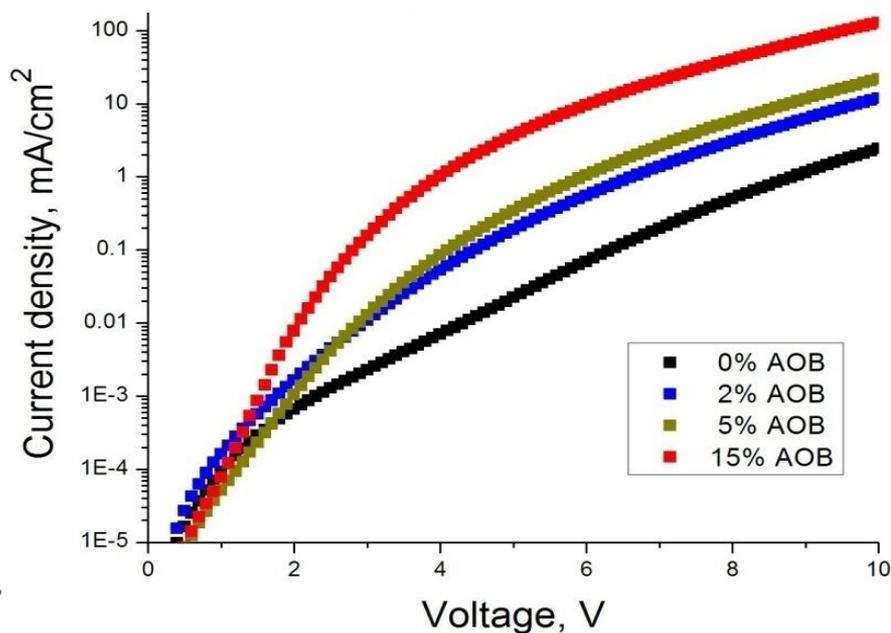
Undoped:
ITO/MTDATA/
CBP:5%PQIr/
BPhen/LiF/Al

p-i-n doped:
ITO/MTDATA:2%F6-TNAP/
CBP:5%PQIr/
BPhen:2%Cs₂CO₃/Al

p-i-n doped, with buffers:
ITO/MTDATA:2%F6-TNAP/5nm
MTDATA/
CBP:5%PQIr/
5nm BPhen/BPhen:2%Cs₂CO₃/Al

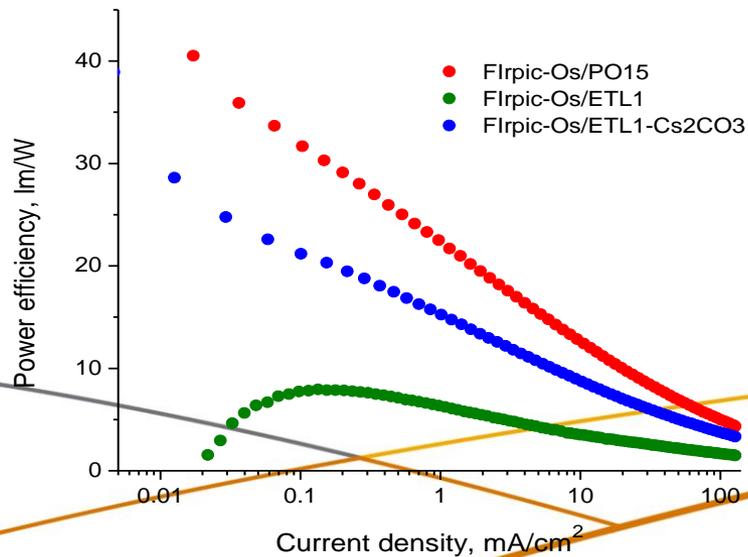
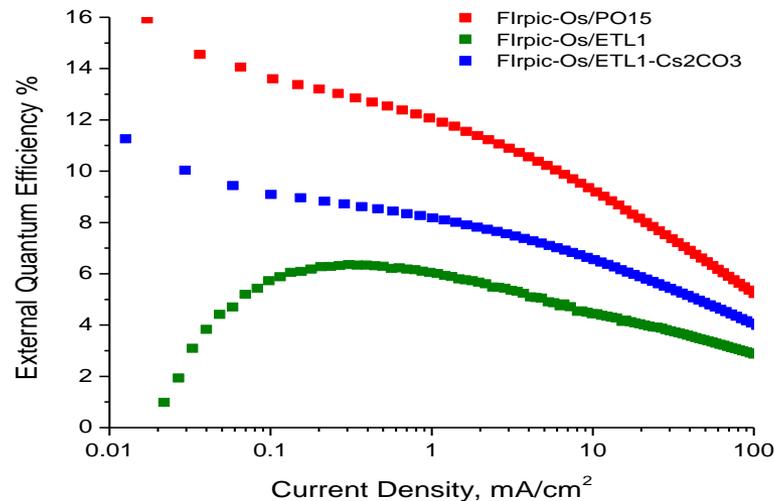
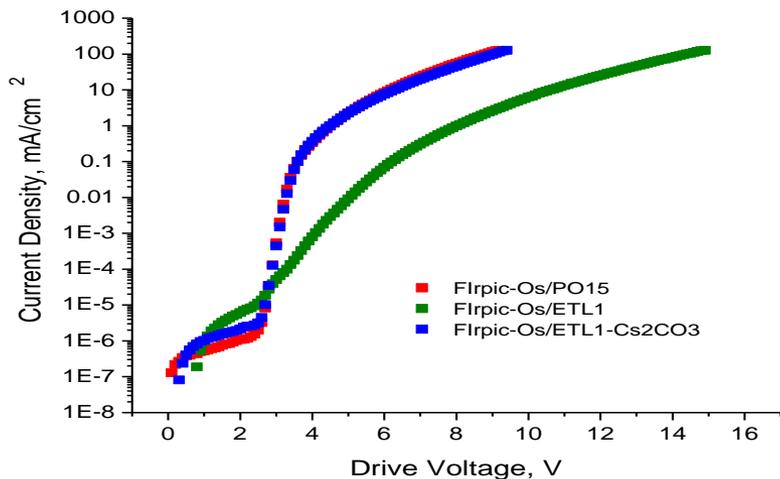
ETM1

- ▶ Synthesized new ETL material with good yield
- ▶ Stable in air, as complex
- ▶ Vacuum deposited
- ▶ Electron-only devices - ITO/20 nm Al/100 nm ETL1:x% dopant/LiF/Al



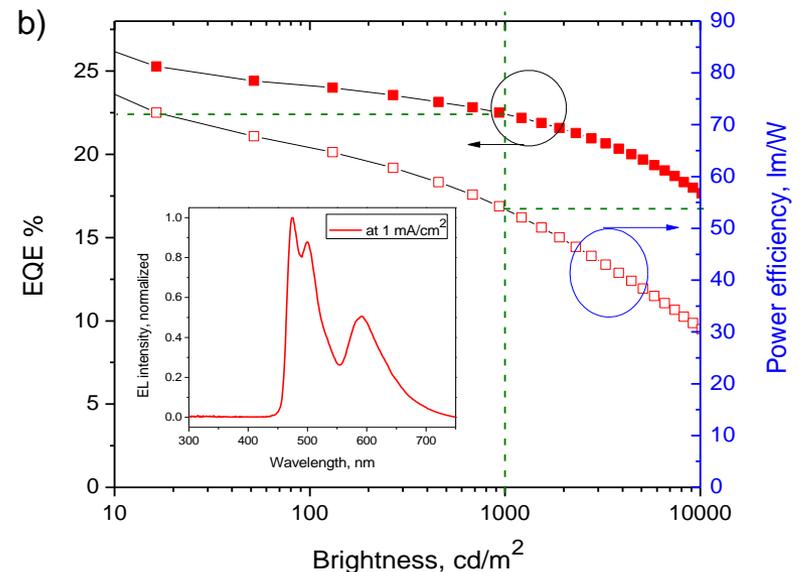
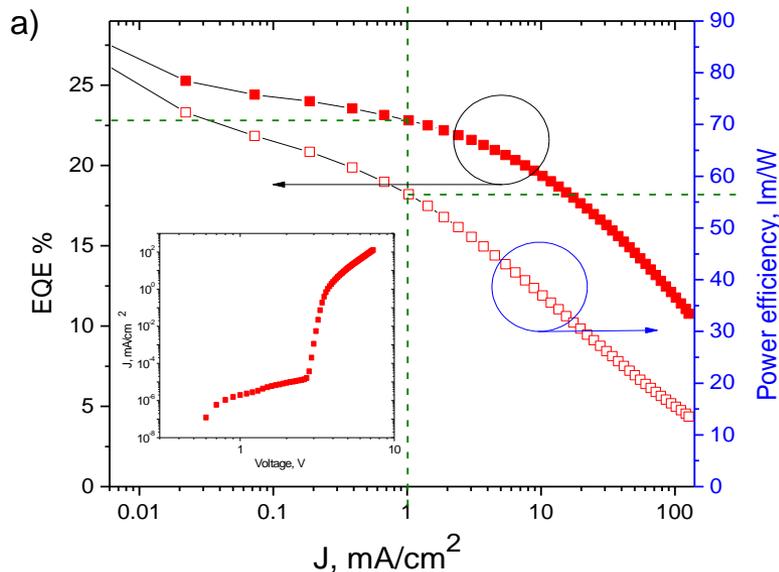
White n-doped OLED with ETL1 vs. PO15

ITO/390 NPD/50 TCTA/150 HMA1:5% Firpic/50 HMA1:1% Os-Orange/100 PO15/400 ETL/Al
ETL: PO15/LiF, ETL1 or ETL1:CsCO₃



- ▶ ETL1:CsCO₃ equals PO15 I-V performance
- ▶ Lower EQE for device not yet optimized

White *p-i-n* device demonstrates good power efficiency (with outcoupling)



ITO/570 Å TPD:1% F3-TCNQ-AdI/300 Å NPD/50 Å TCTA/80 Å HMA1:10%
 Firpic:0.5% Os-Orange/100 Å PO15/350 Å BPhen/50 Å
 ETM:8%Cs₂CO₃/10 Å LiF/1000 Å Al

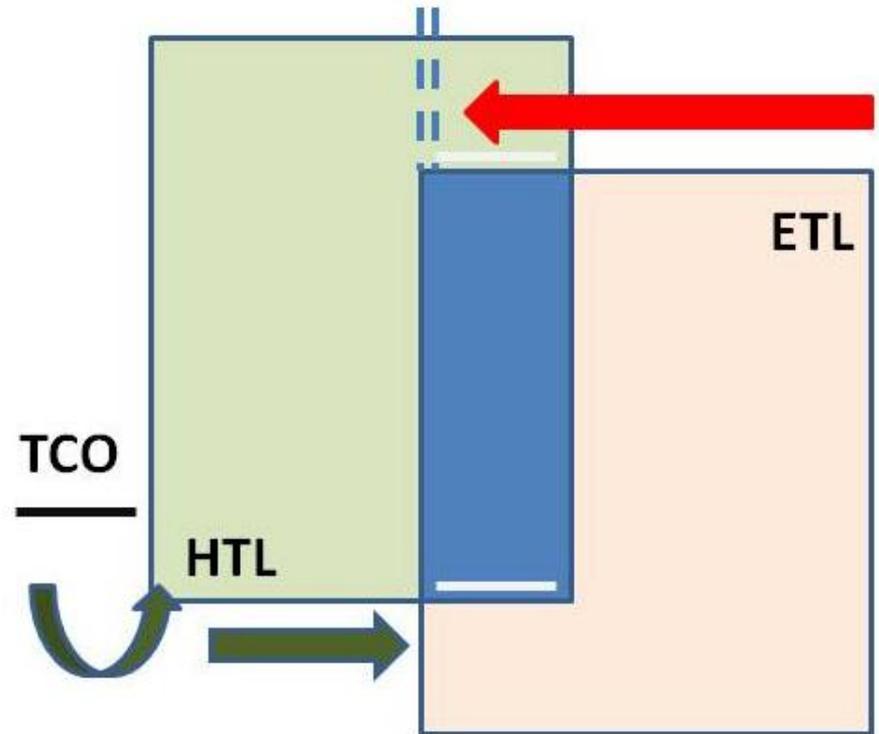
Outline

- ▶ Conductivity doping
- ▶ **New charge transport layers**
- ▶ Summary

Design Rules

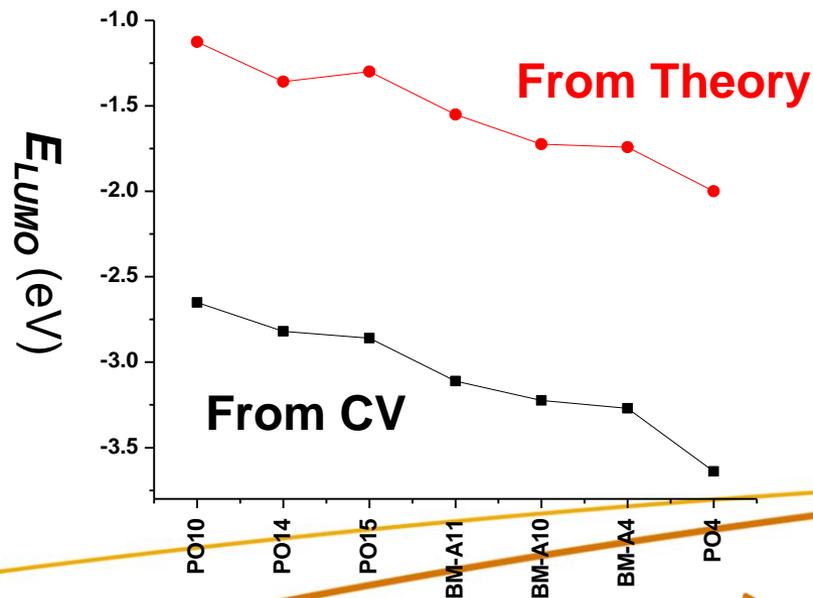
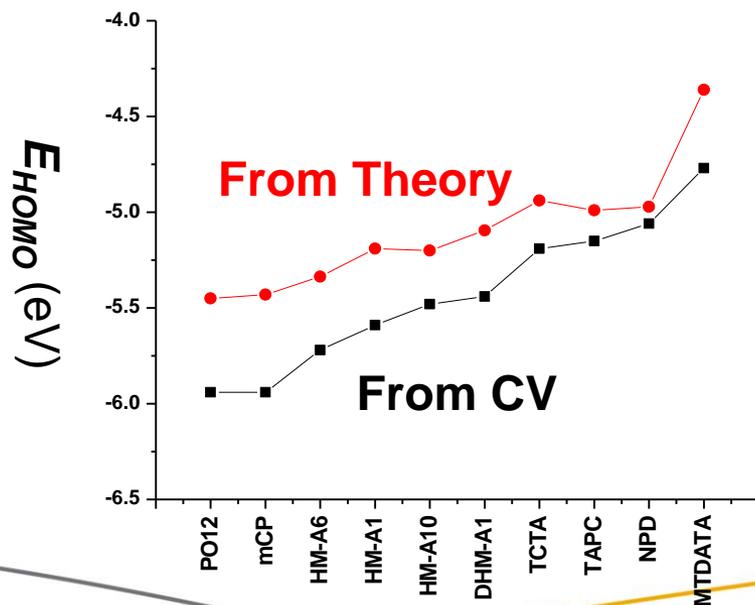
- Hole transport materials

- ▶ Hole injection
 - Shallow E_{HOMO}
- ▶ Hole transport
 - High hole mobility
- ▶ Electron blocking
 - Shallow E_{LUMO}
- ▶ Prevent exciton quenching
 - High triplet energy

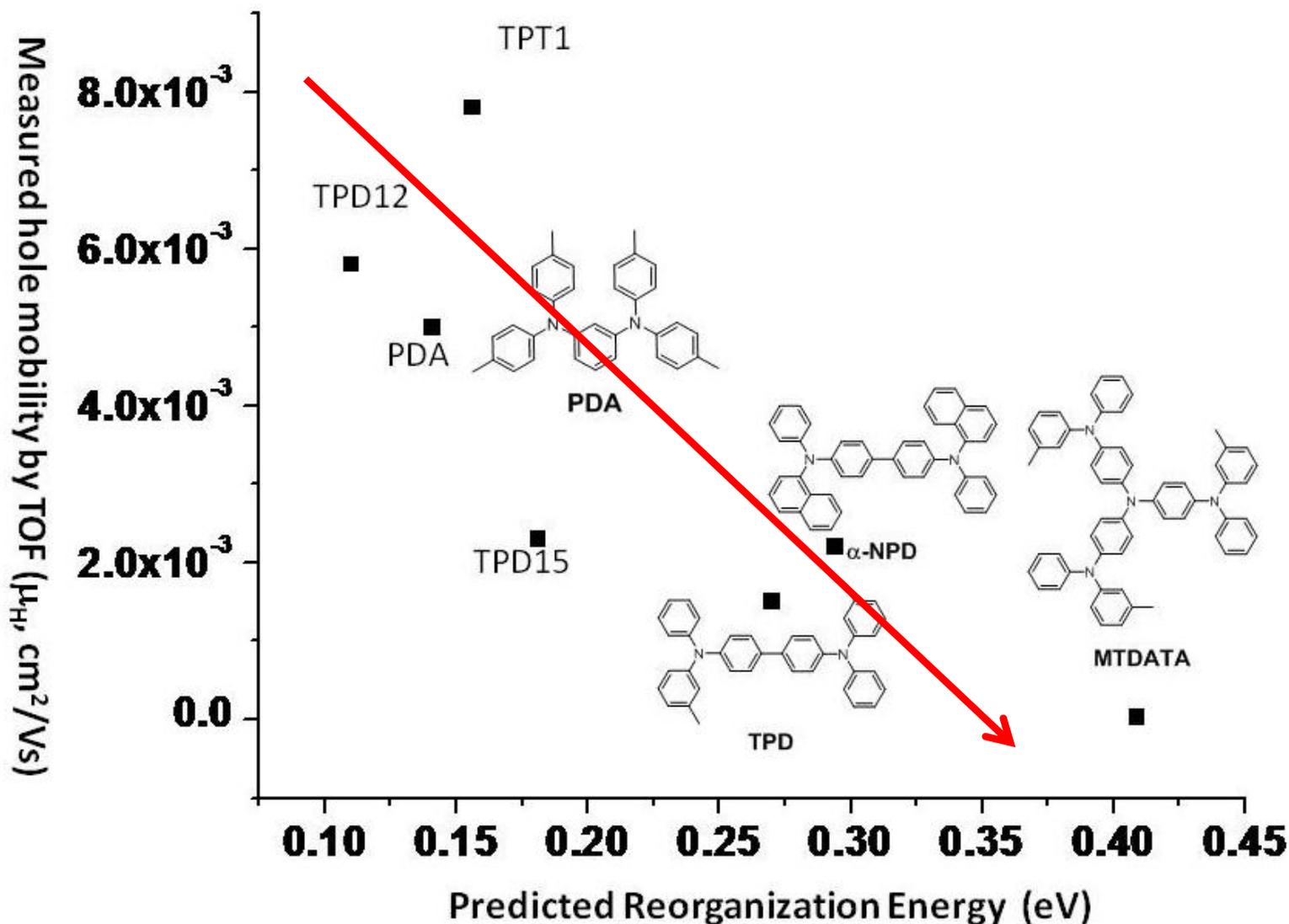


Computational Design - HOMO/LUMO energies

- ▶ Geometry optimized at B3LYP/6-31G* level
- ▶ *NWChem* computational package

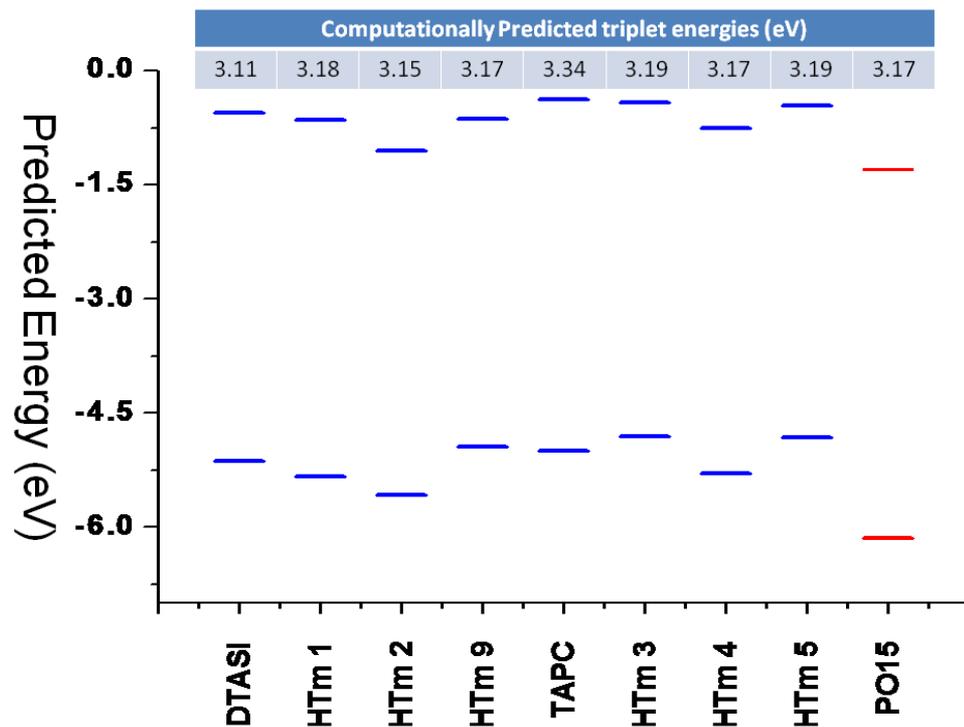


Computational Design - reorganization energy vs. mobility



Rational Design of HTMs

- ▶ Two classes of HTMs based on TAPC and DTASI were studied
- ▶ Predicted three parameters:
 - Reorganization energy (λ_i)
 - E_{HOMO} / E_{LUMO}
 - E_T

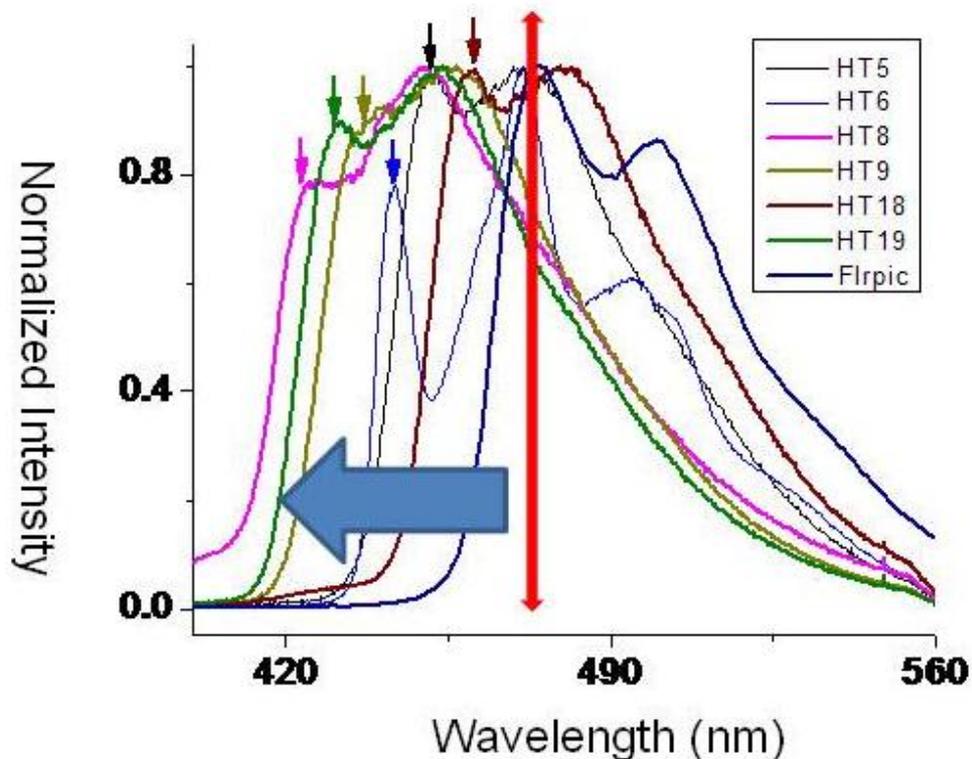


Reorganization Energies			
DTASI	0.095	TAPC	0.104
HTm 1	0.104	HTm 3	0.070
HTm 2	0.064	HTm 4	0.059
HTm 9	0.057	HTm 5	0.072

E_T calculated as described by Bredas
Chem. Mater., **2010**, 22 (1), 247–254

Measured electronic structure for new HTMs

	E_{LUMO} (eV)	E_{HOMO} (eV)	E_g (eV)
TAPC	-1.7	-5.2	3.5
HTM 5	-1.7	-5.3	3.6
HTM 6	-1.7	-5.2	3.6
HT8	-1.6	-5.1	3.5
DTASI	-1.8	-5.3	3.4
HTM 9	-1.8	-5.2	3.5
HTM 18	-1.9	-5.4	3.5
HTM 19	-1.9	-5.4	3.5
PO15	-2.9	-6.6	3.7



All HTm have $E_T > E_T$ of Flrpic

$$E_{LUMO} = E_{HOMO} + E_g$$

$$E_{HOMO} = (1.4 \pm 0.1) \cdot (qV_{CV}) (4.6 \pm 0.08) \text{ eV}$$

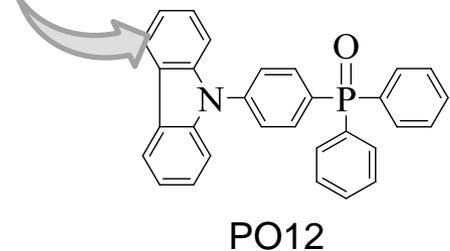
D' Aandrade Organic Electronics 6 (2005) 11–20

Summary and Future Work



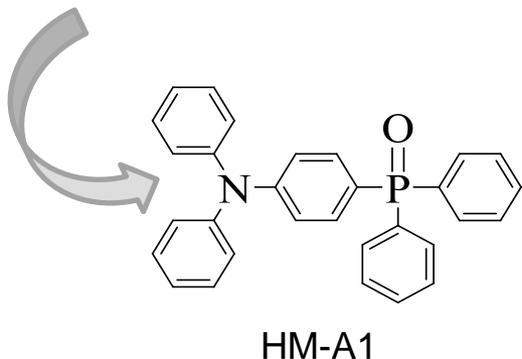
Electron transporting
Host

EQE ~ 10% at 20% Flrpic doping



Ambipolar Host

EQE ~ 8% at 5% Flrpic doping



Ambipolar Host

EQE ~ 16%
PE – 38 lm/W
Improved hole injection
Hole rich

Mixed host structure

Develop new HTMs
Improve
- Charge balance
- Stability

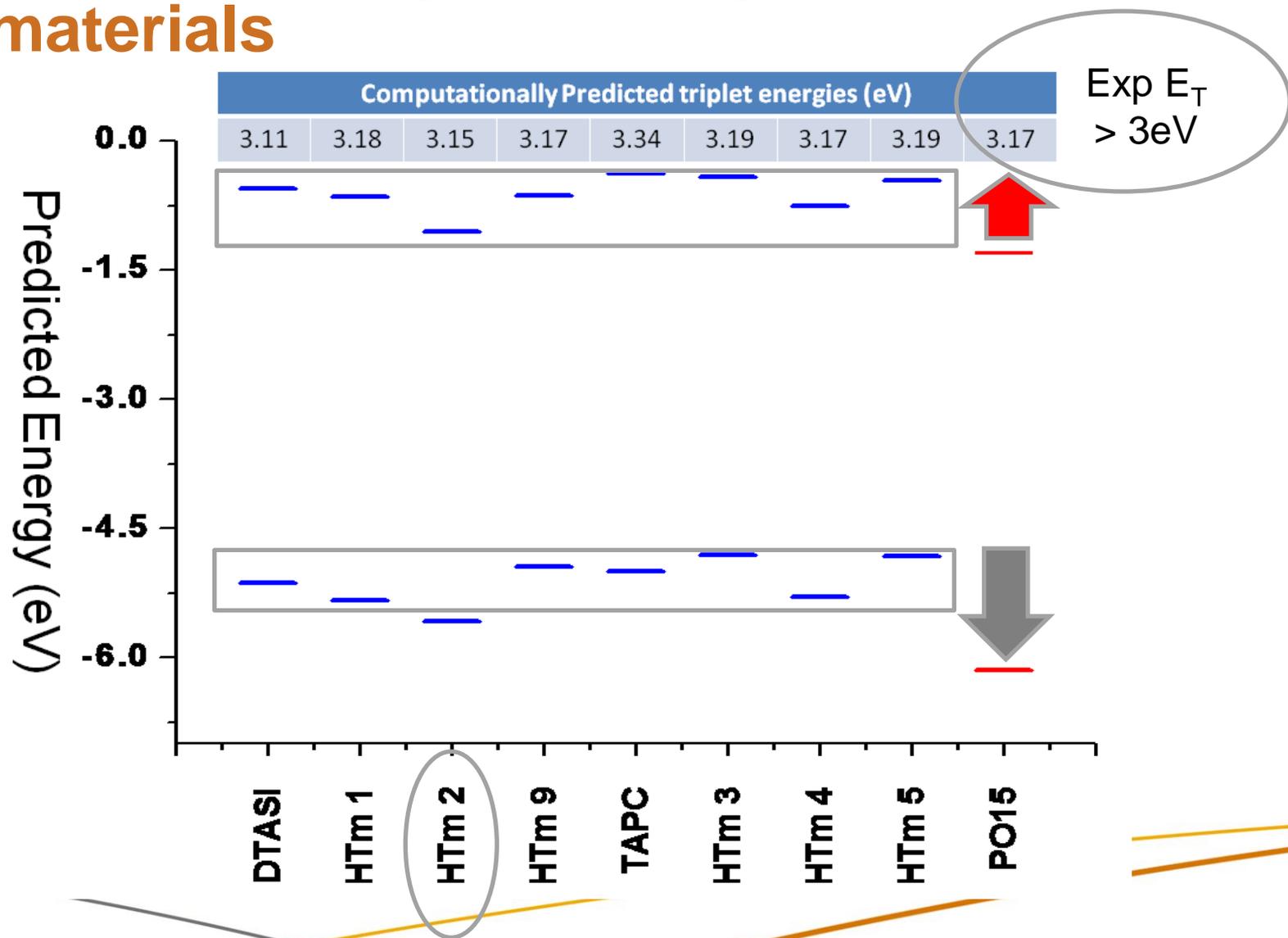
Mixed host structure

EQE ~ 17%
PE > 50 lm/W
Improved charge balance

Charge transport materials

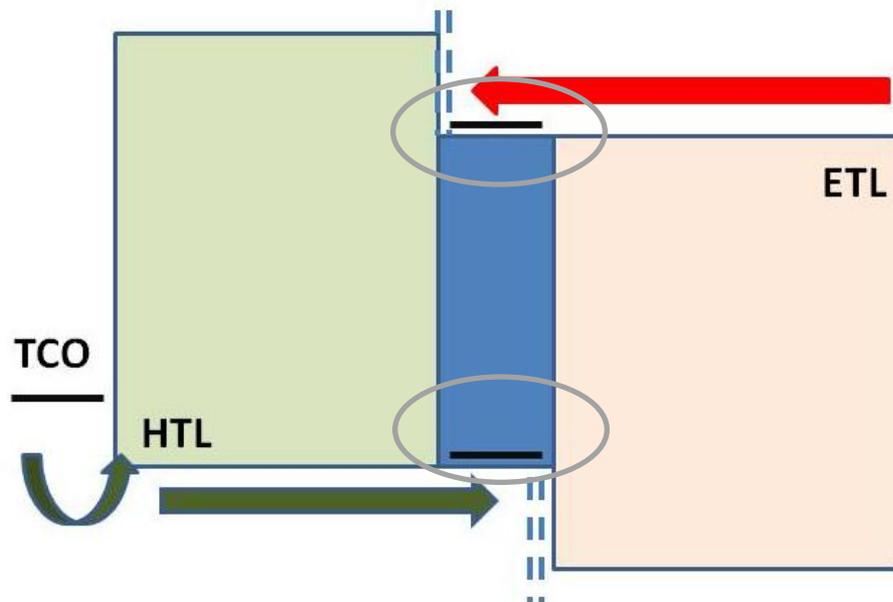
- ▶ Goal: Add to the toolbox of stable charge transport materials suitable for blue OLEDs
 - Reduce roll-off
 - Improve charge balance in EML
 - Improve process window
- ▶ Examples – HTLs, ambipolar hosts

Rational Design of charge transport materials



Design rules for ambipolar hosts

- ▶ Hole injection
 - Shallow E_{HOMO}
- ▶ Charge transport
 - High hole mobility
 - High electron mobility
- ▶ Prevent exciton quenching
 - High triplet energy
- ▶ Prevent charge trapping



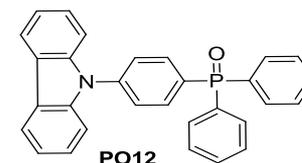
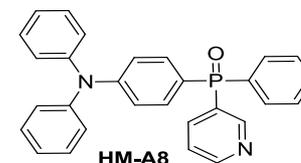
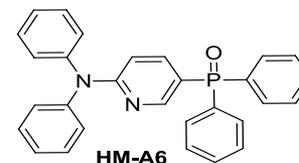
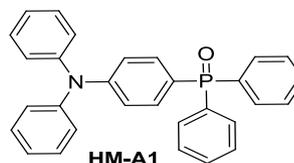
Alter device properties by molecular design of ambipolar hosts

► Simple changes to the structure

- Change E_T
- Change E_{HOMO}/E_{LUMO}
- Change packing
- Change transport

► Affect the charge balance in the EML

► Affect the device efficiency

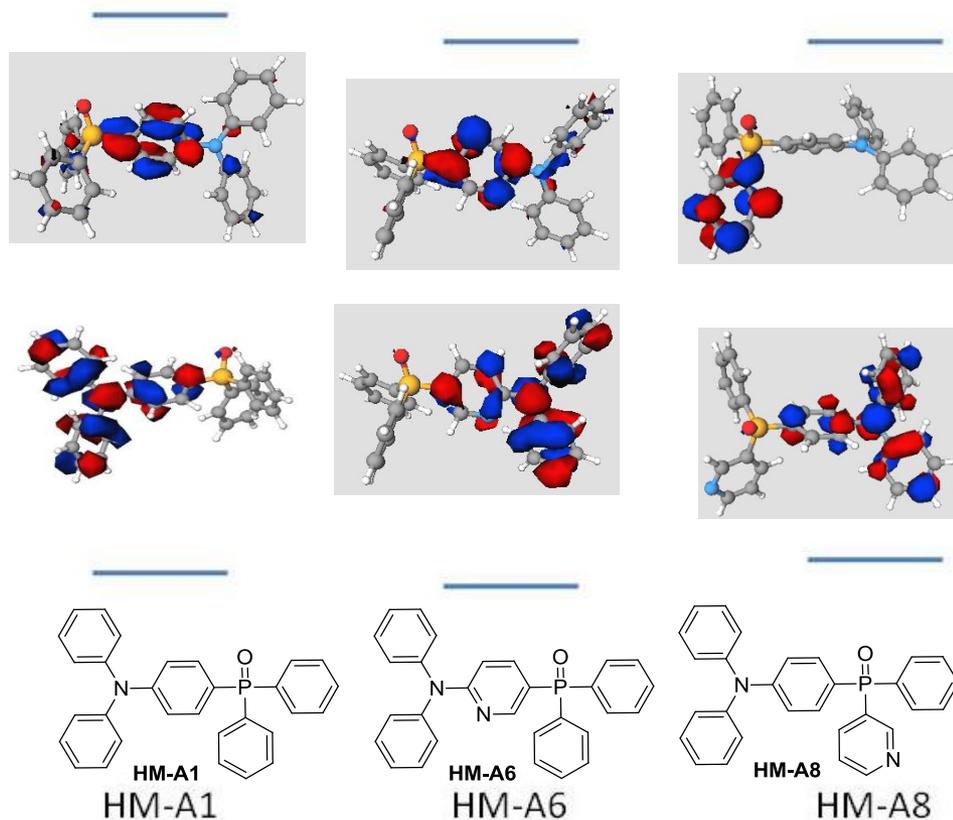


	E_{HOMO}, eV	E_{LUMO}, eV	E_T, eV
PO12	-5.70	-2.52	3.00
HM-A1	-5.45	-2.56	2.80
HM-A6	-5.54	-2.68	2.80
HM-A8	-5.39	-2.69	2.82

Tuning hole transport: phenyl vs. pyridyl moieties

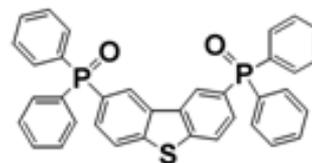
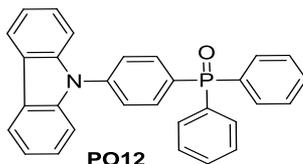
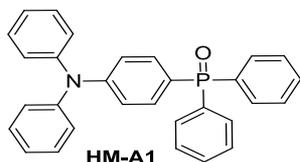
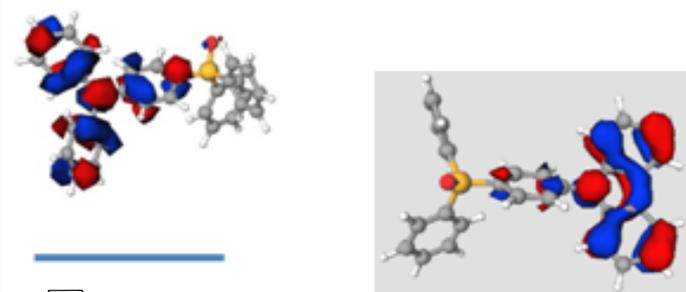
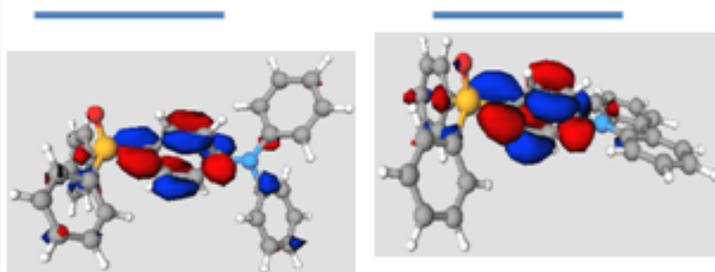
- ▶ HTm = TPA
- ▶ HM-A6 and HM-A8 have similar LUMO energies
- ▶ LUMO changes
- ▶ HM-A8:
 - The HTm does not contain an electron deficient ring

Energy estimated by CV (eV)



Tune electronic structure by changing the HTm - CBz vs. TPA

Energy estimated by CV (eV)



E_{LUMO} unchanged

HOMO on the HTm

■ E_{HOMO} different

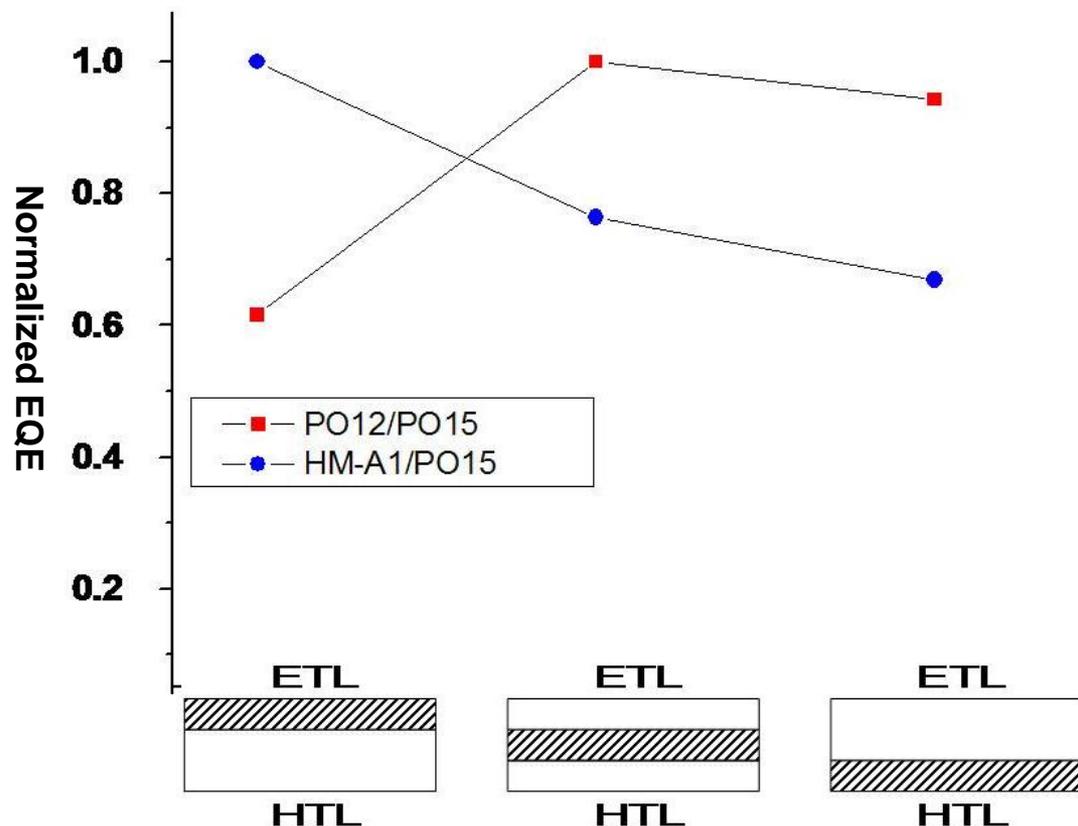
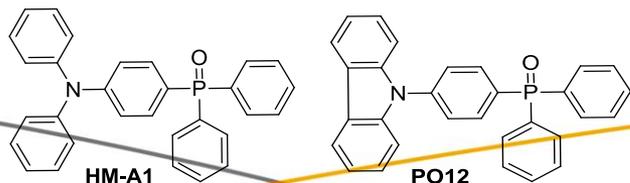
HM-A1

PO12

PO15

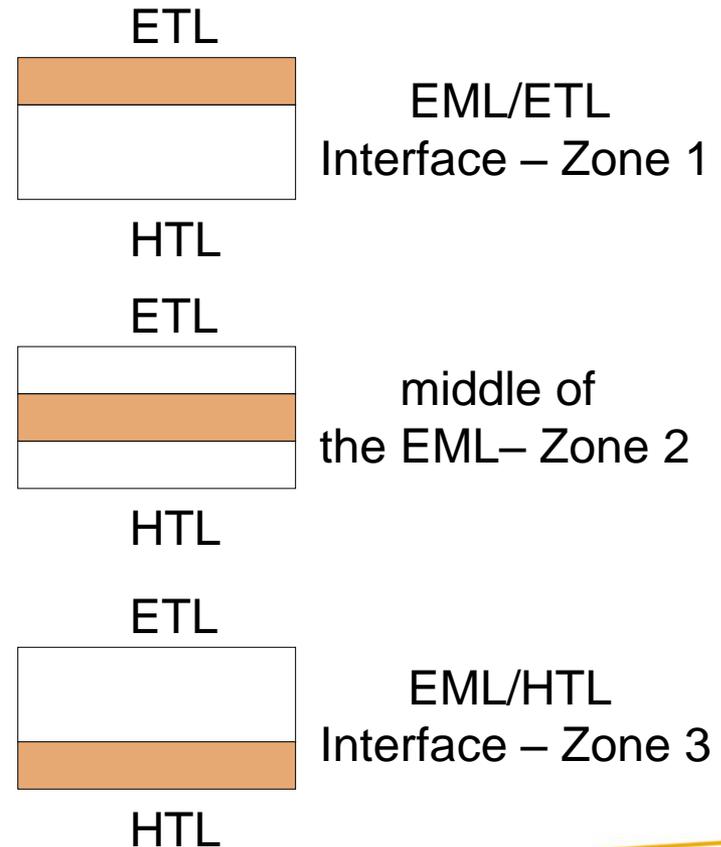
Tuning mobility: CBz vs. TPA

- ▶ HM-A1 devices are hole-rich
- ▶ Most of the emission occurs far away from the HTL interface
- ▶ Hole transport by TPA is more efficient than by CBz – higher mobility



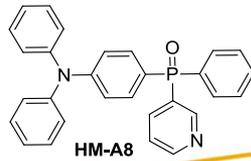
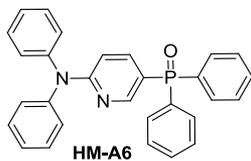
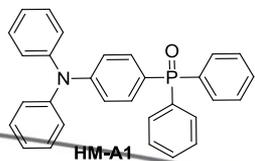
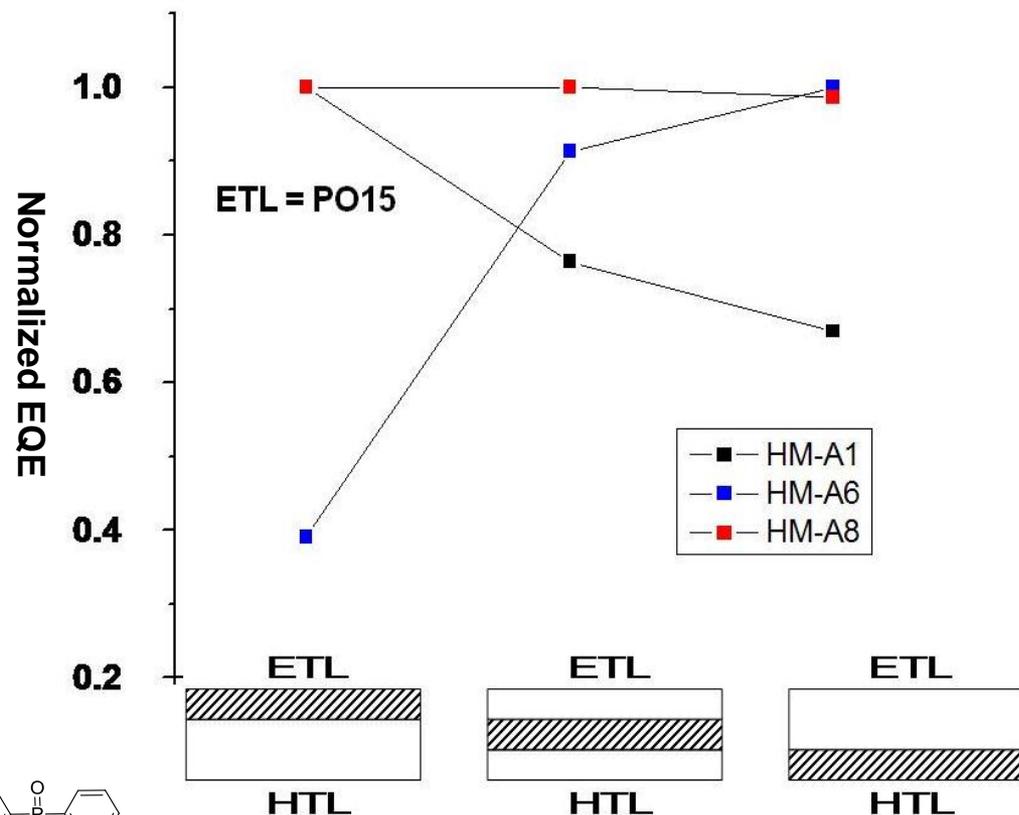
Probe charge balance by location of the recombination zone

- ▶ Emission zone location related to relative charge transport within the EML
- ▶ Host materials with:
 - holes > electrons = Zone 1
 - electrons > holes = Zone 3
 - holes ~ electrons = Zone 2

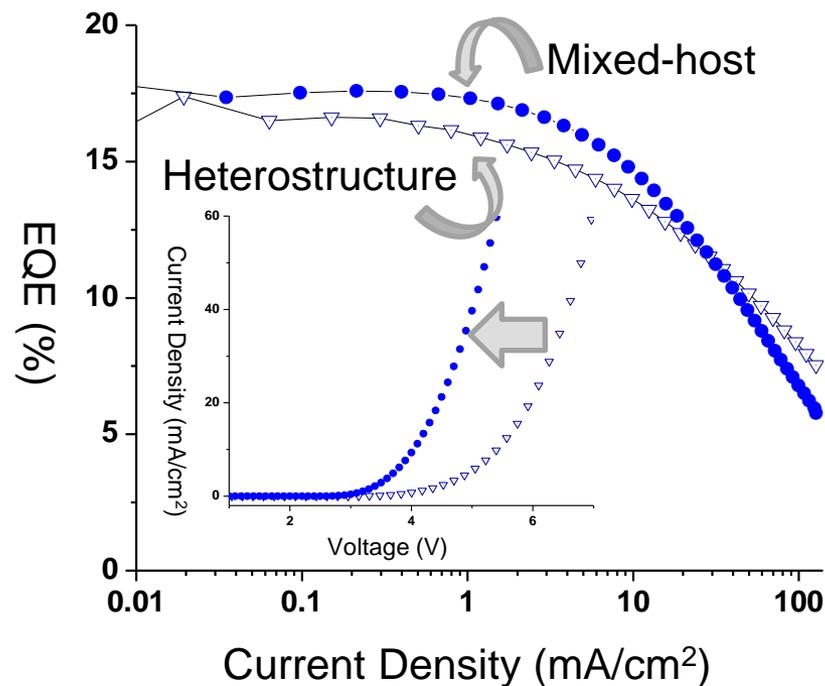
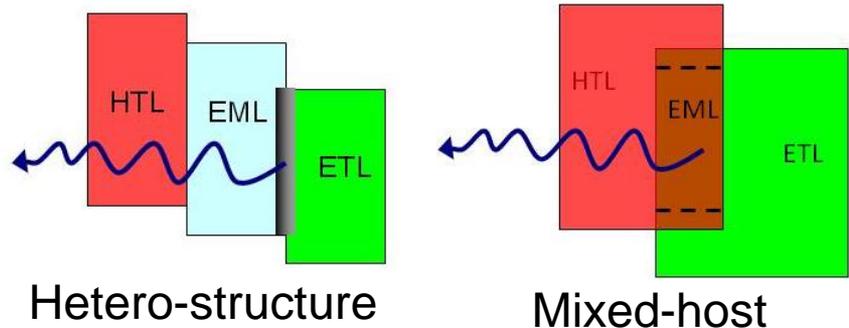


Effect of the position of the LUMO on the emission zone

- ▶ HM-A1 is hole rich
- ▶ HM-A6 is electron rich
- ▶ HM-A8 is closer to truly ambipolar



Blue OLEDs: baseline devices



	Voltage (V)	EQE (%)	h_p (lm/W)
Hetero-structure	5% Flrpic:HMA1		
	4.1	16.4 %	38.3
Mixed host structure	TAPC(35%):PO15(60%):Flrpic(5%)		
	3.2	17.2 %	52.0
@ $1\text{mA}/\text{cm}^2$	35nm HTL/15nm EML/50nm ETL/LiF-AI		

Summary

- ▶ Conductivity dopants can reduce voltage, but...
 - Trade-off between efficiency and device complexity – implications for manufacturing?
- ▶ Interface doping is currently done ‘intrinsically’ – i.e., LiF or NaF EIL or H⁺ for acidic HIL
 - Can do this more deliberately if necessary
- ▶ Designing host, ETL and HTL for high-efficiency blue (and white) devices requires understanding of the system
 - Device architecture directly impacts molecular design